



Description

The HD7258 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 30A$

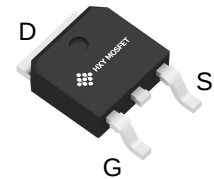
$R_{DS(ON)} < 43m\Omega$ @ $V_{GS}=10V$

Application

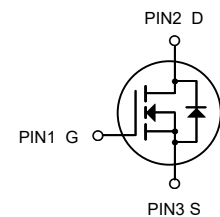
Battery protection

Load switch

Uninterruptible power supply



TO-252-2L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HD7258	TO252-2L	HD7258 XXYYS	2500

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	30	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	13.5	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	4.2	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	3.4	A
I_{DM}	Pulsed Drain Current ²	45	A
EAS	Single Pulse Avalanche Energy ³	36.5	mJ
I_{AS}	Avalanche Current	27	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	52.1	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.4	$^{\circ}C/W$



Electrical Characteristics (T_c=25°C unless otherwise noted)

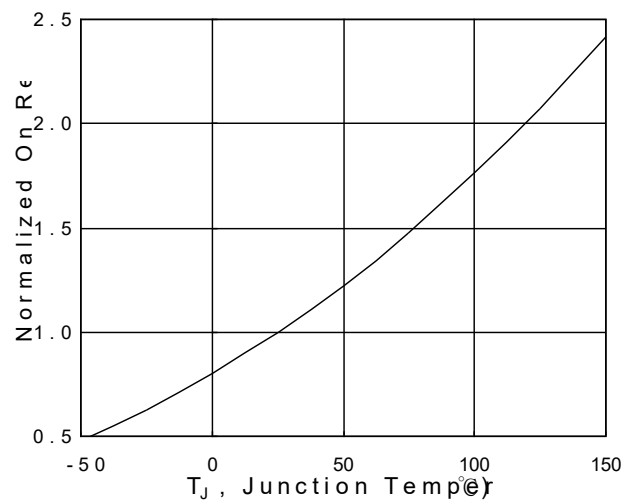
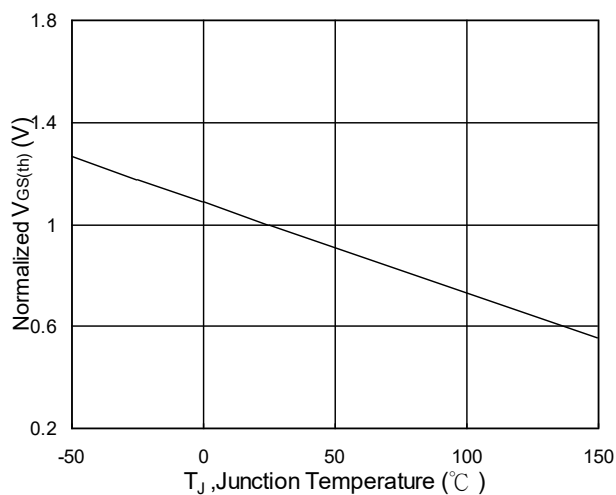
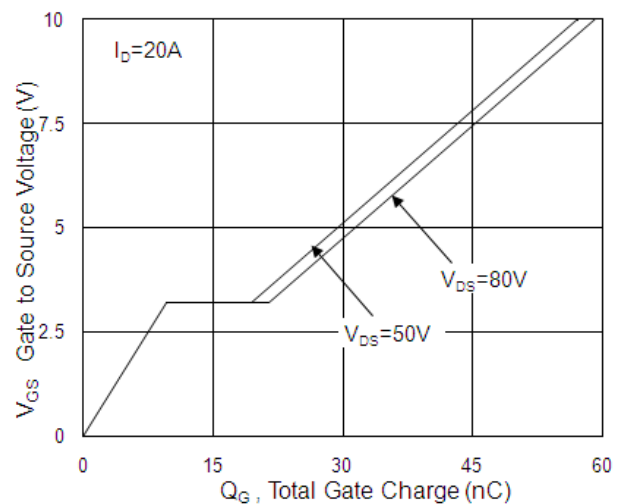
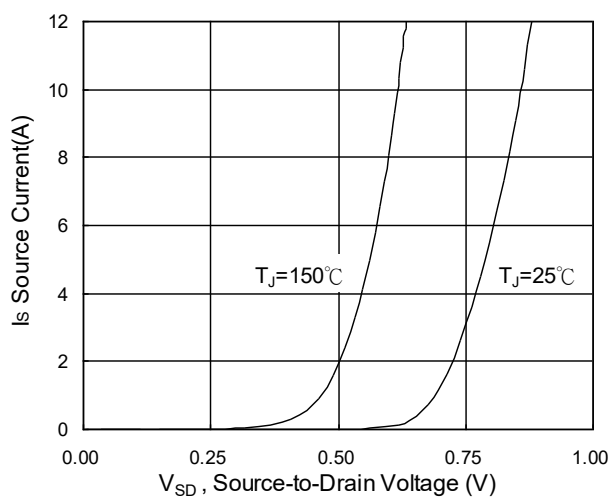
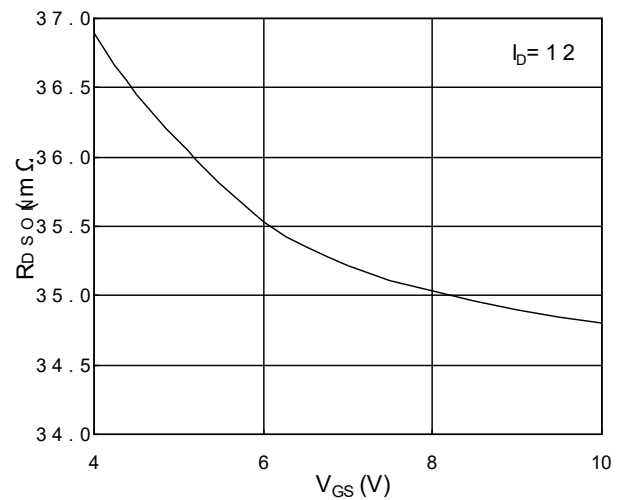
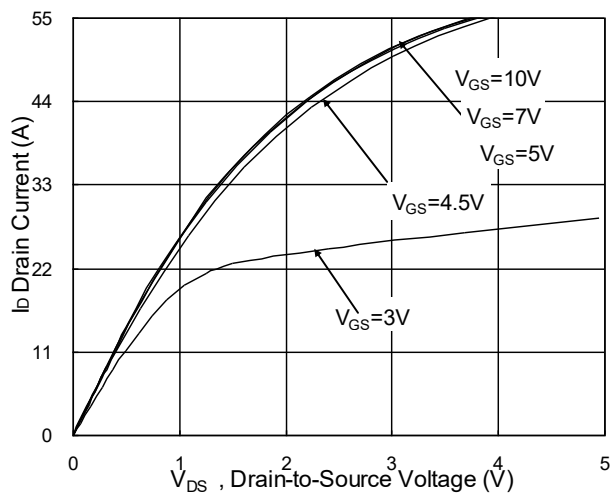
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	35	43	mΩ
		V _{GS} =4.5V, I _D =15A	---	40	50	
V _{GS(th)}	Gate Threshold Voltage		1.3	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA	---	-5.52	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	10	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	28.7	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.6	3.2	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =20A	---	60	84	nC
Q _{gs}	Gate-Source Charge		---	9.7	14	
Q _{gd}	Gate-Drain Charge		---	11.8	16.5	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =20A	---	10.4	21	ns
T _r	Rise Time		---	46	83	
T _{d(off)}	Turn-Off Delay Time		---	54	108	
T _f	Fall Time		---	10	20	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3848	5387	pF
C _{oss}	Output Capacitance		---	137	192	
C _{rss}	Reverse Transfer Capacitance		---	82	115	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	22	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	45	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=100A/μs, T _J =25°C	---	30	---	nS
Q _{rr}	Reverse Recovery Charge		---	37	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=27A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics



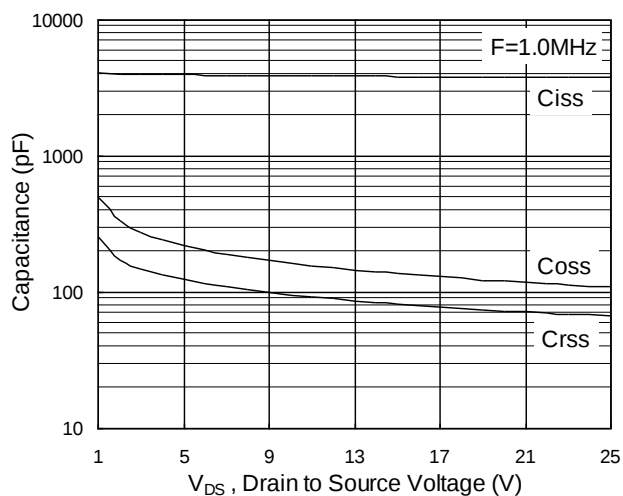


Fig.7 Capacitance

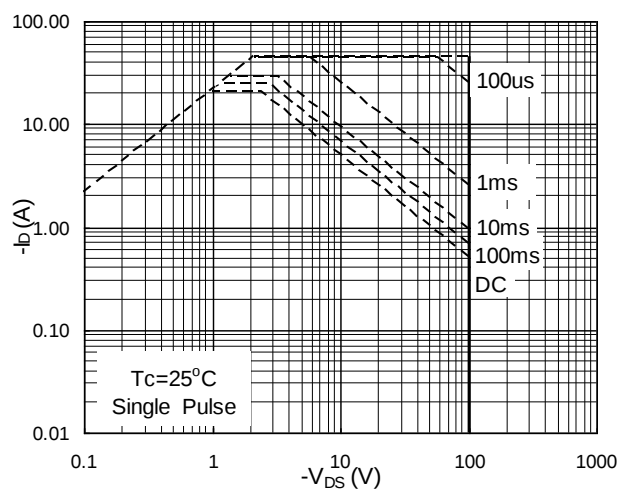


Fig.8 Safe Operating Area

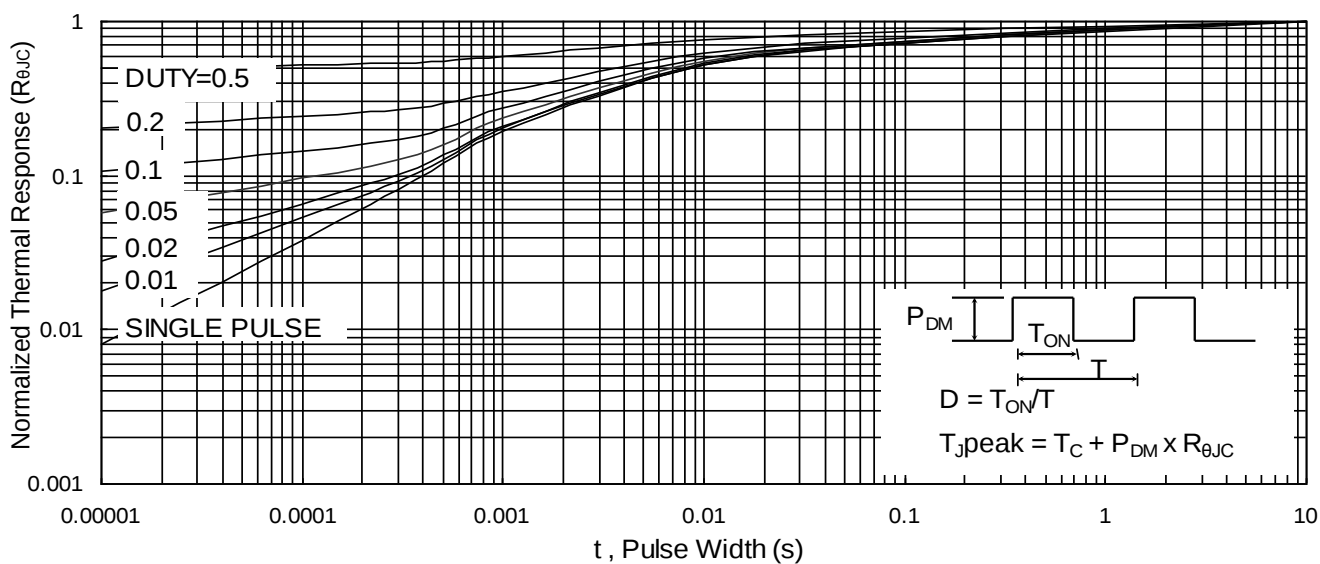


Fig.9 Normalized Maximum Transient Thermal Impedance

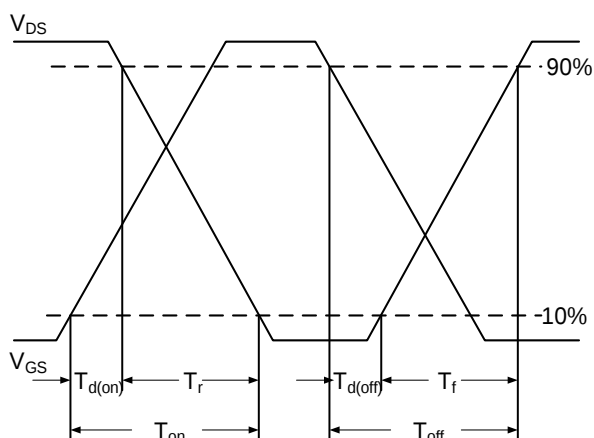


Fig.10 Switching Time Waveform

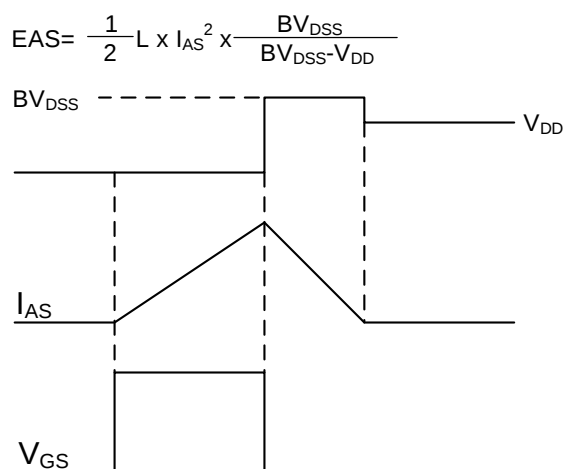


Fig.11 Unclamped Inductive Switching Waveform



N-Channel Enhancement Mode MOSFET

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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